

FEATURES

- 4 X 5.0 mm square active area
- Low dark current & capacitance
- Fast rise times
- High QE at 1064 nm

DESCRIPTION

4 X 25.0 mm² NIR enhanced Quadrant PIN Photodiode with 50 μm gaps. Surface mount packaged with a fused silica window.

APPLICATIONS

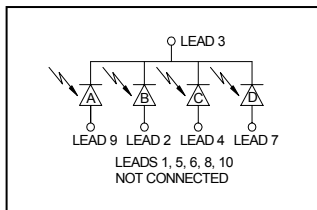
- Pulsed 1064 nm laser detection
- NIR pulsed light sensor
- High speed photometry



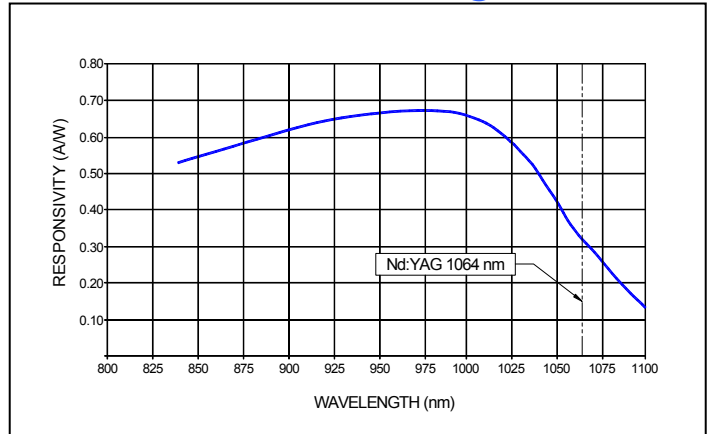
ABSOLUTE MAXIMUM RATING

SYMBOL	PARAMETER	MIN	MAX	UNITS
T _{STG}	Storage Temp	-15	+80	°C
T _{OP}	Operating Temp	-15	+70	°C
V _{R(OP)}	Reverse Operating Voltage	-	200	V
I _(PEAK)	Peak DC Current	-	10	mA

SCHEMATIC



SPECTRAL RESPONSE @ 23°C



ELECTRO-OPTICAL CHARACTERISTICS @ 23° C

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _D	Dark Current*	V _R = 150 V; @ 23°C	---	20	---	nA
		V _R = 150 V; @ 60°C	---	300	---	
C	Capacitance*	V _R = 150 V	---	25	---	pF
	Responsivity	V _R = 150 V; λ = 1064 nm; @ 23°C	---	0.30	---	A/W
		V _R = 150 V; λ = 1064 nm; @ 60°C	---	0.40	---	
V _{BR}	Breakdown Voltage	I _R = 10 μA	250	---	---	V
t _r	Rise Time	V _R = 150 V; λ = 1064 nm; RL = 50 Ω	---	6	---	ns
	Uniformity of Response	V _R = 150 V; λ = 1064 nm; @ 23°C	---	2	5	%
		V _R = 150 V; λ = 1064 nm; @ 23°C	---	2	5	

* per element

Disclaimer: Due to our policy of continued development, specifications are subject to change without notice.

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